March 2008

FAIRCHILD

SEMICONDUCTOR®

FFPF60SB60DS

Features

- High Speed Switching, t_{rr} < 25ns @ I_F = 4A
- High Reverse Voltage and High Reliability
- RoHS compliant

Applications

- General Purpose
- Switching Mode Power Supply
- Boost Diode in continuous mode power factor corrections
- Power switching circuits

4A, 600V STEALTH™ II Rectifier

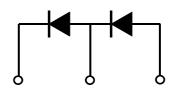
The FFPF60SB60DS is STEALTH[™] II rectifier with soft recovery characteristics. It is silicon nitride passivated ion-implanted epitaxial planar construction.

STEALTHTM II Rectifier

This device is intended for use as freewheeling of boost diode in switching power supplies and other power swithching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.







1. Cathode 2. Anode(Cathode) 3. Anode

Absolute Maximum Ratings $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{RRM}	Peak Repetitive Reverse Voltage	600	V	
V _{RWM}	Working Peak Reverse Voltage	600	V	
V _R	DC Blocking Voltage	600	V	
I _{F(AV)}	Average Rectified Forward Current $@ T_{C} = 100^{\circ}C$	4	A	
I _{FSM}	Non-repetitive Peak Surge Current 60Hz Single Half-Sine Wave	40	А	
T _J , T _{STG}	Operating and Storage Temperature Range	-65 to +150	°C	

Thermal Characteristics

Symbol	Parameter	Ratings	Units
$R_{ ext{ heta}JC}$	Maximum Thermal Resistance, Junction to Case	8.7	°C/W

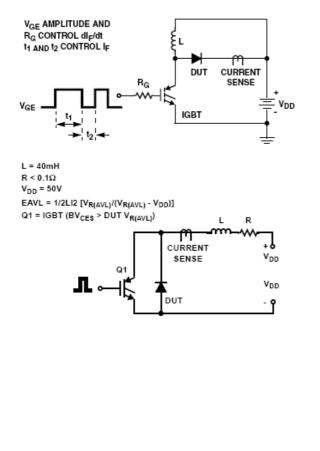
Package Marking and Ordering Information

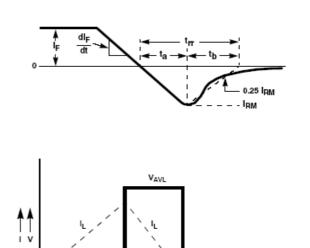
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FFPF60SB60DS	FFPF60SB60DSTU	TO220F	-	-	50

Symbol	Parameter		Min.	Тур.	Max.	Units
V _{FM} 1	$I_F = 4A$ $I_F = 4A$	T _C = 25°C T _C = 125°C	-	2.2 1.7	2.6	V
I _{RM} 1	$V_{R} = 600V$ $V_{R} = 600V$	$T_{C} = 25^{\circ}C$ $T_{C} = 125^{\circ}C$		-	100 500	μΑ
t _{rr}	I _F = 1A, di/dt = 100A/µs, V _R = 30V	$T_{C} = 25^{\circ}C$	-	16	23	ns
t _{rr} I _{rr} S factor Q _{rr}	I _F = 4A, di/dt = 200A/µs, V _R = 390V	$T_{\rm C} = 25^{\rm o}{\rm C}$		18 2 0.7 18	25 - - -	ns A nC
t _{rr} I _{rr} S factor Q _{rr}	I _F = 4A, di/dt = 200A/µs, V _R = 390V	T _C = 125°C		45 2.8 1.8 64	- - -	ns A nC
W _{AVL}	Avalanche Energy (L = 40mH)		5	-	-	mJ

Notes: 1: Pulse: Test Pulse width = 300µs, Duty Cycle = 2%

Test Circuit and Waveforms





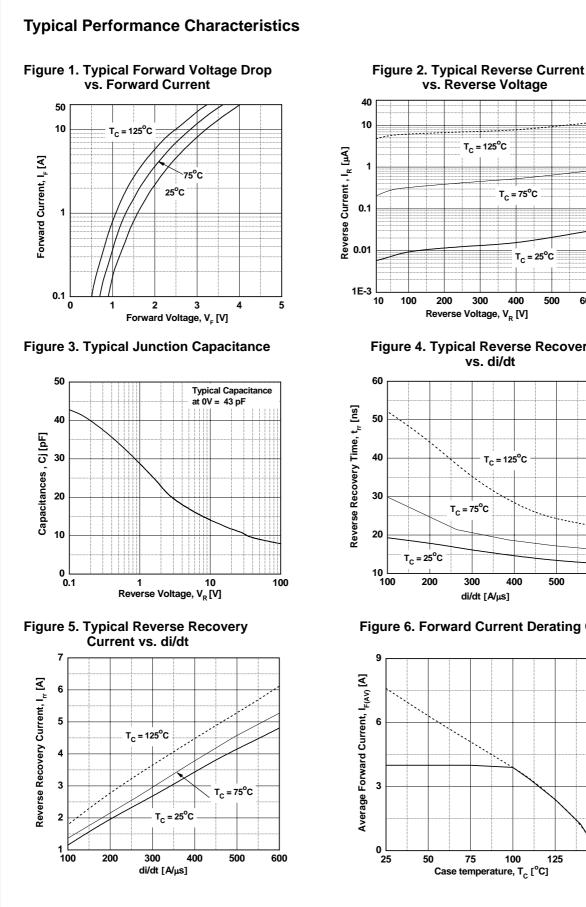
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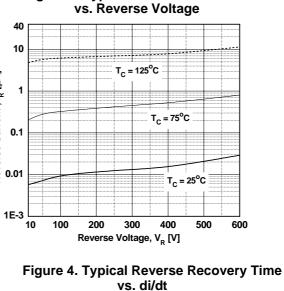
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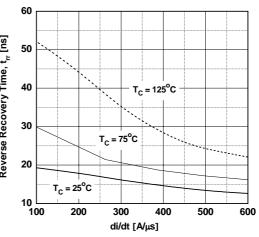
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t0

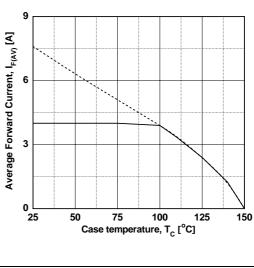
FFPF60SB60DS



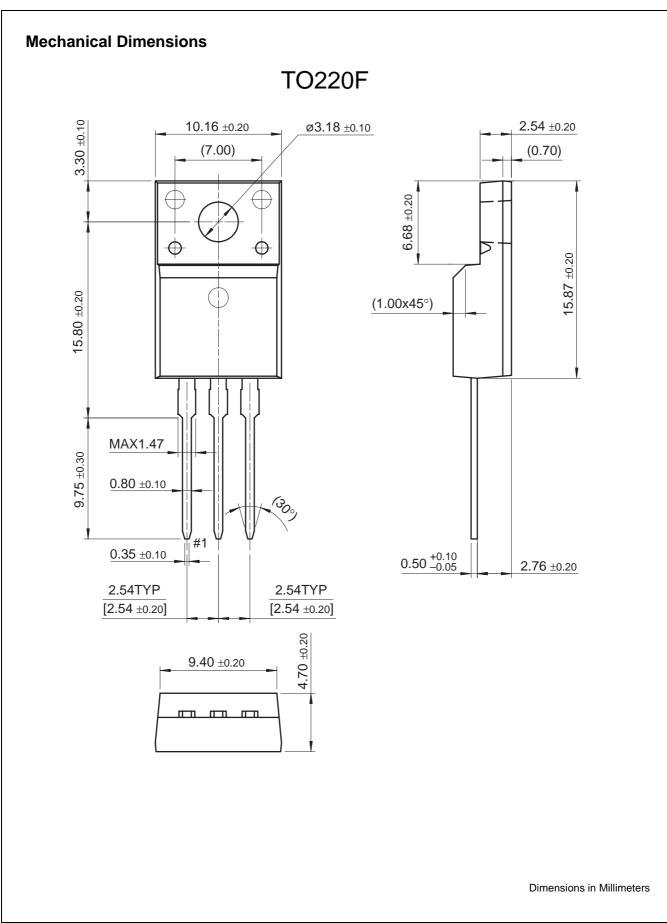








FFPF60SB60DS Rev. A



FFPF60SB60DS



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FPS™

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